



Three-Dimensional Reduced Graphene Oxide Network on Copper Foam as High-performance Supercapacitor Electrodes

Dey, Ramendra Sundar; Chi, Qijin

Publication date:
2014

Document Version
Publisher's PDF, also known as Version of record

[Link back to DTU Orbit](#)

Citation (APA):
Dey, R. S., & Chi, Q. (2014). *Three-Dimensional Reduced Graphene Oxide Network on Copper Foam as High-performance Supercapacitor Electrodes*. Abstract from 65th Annual Meeting of the International Society of Electrochemistry, Lausanne, Switzerland.

General rights

Copyright and moral rights for the publications made accessible in the public portal are retained by the authors and/or other copyright owners and it is a condition of accessing publications that users recognise and abide by the legal requirements associated with these rights.

- Users may download and print one copy of any publication from the public portal for the purpose of private study or research.
- You may not further distribute the material or use it for any profit-making activity or commercial gain
- You may freely distribute the URL identifying the publication in the public portal

If you believe that this document breaches copyright please contact us providing details, and we will remove access to the work immediately and investigate your claim.

Three-Dimensional Reduced Graphene Oxide Network on Copper Foam as High-performance Supercapacitor Electrodes

Ramendra Sundar Dey, Qijin Chi*

Department of Chemistry, Technical University of Denmark, 2800 Kongens Lyngby, Denmark.
(E-mail: ramdey@kemi.dtu.dk)

Electrochemically generated copper foam (Cuf) could serve as an effective template for fabrication of three-dimensional (3D) reduced graphene oxide (rGO) networks. Here we present a facile approach to preparation of 3D rGO network supported by Cuf as binder-free and current collector-integrated supercapacitor electrodes (3DrGO@Cuf) [1]. The method involves a two-step procedure, self-assembly of graphene oxide (GO) nanosheets on Cuf and electrochemical reduction of GO into rGO. We have systematically characterized as-synthesized materials using AFM, SEM and XRD to reveal their morphological and structural features. Electrochemical functional tests show that such electrodes are capable of delivering a specific capacitance as high as 623 F g^{-1} at a current density of 1 A g^{-1} . The observed high specific capacitance is most likely attributed to the unique porous structure consisting of highly connected nanoscale pores and high-density capacitive sites. 3DrGO@Cuf electrodes also exhibit considerably high stability over successive charge-discharge switching. For example, over 98 % specific capacitance is retained after 2000 cycles. To the best of our knowledge, we may have achieved the highest specific capacitance with 3DrGO@Cuf electrodes among reported pure 3D graphene materials to date (i.e. 3D graphene materials without doping additional capacitive species) [2, 3].

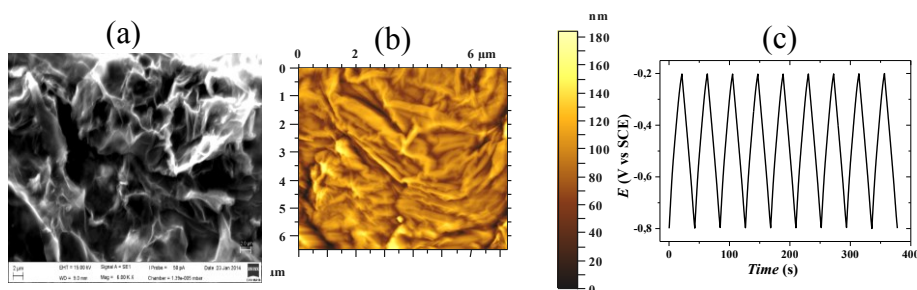


Fig. 1. (a) SEM and (b) AFM image of 3DrGO nanostructures on Cu foam. (c) Charge-discharge profile of 3DrGO@Cuf in 1M PBS (current density: 10 A g^{-1}).

References

- [1] R. S. Dey, Q. Chi, manuscript in submission (2014).
- [2] Z. Niu, J. Chen, H. H. Hng, J. Ma, X. Chen, *Adv. Mater.* 24 (2012) 4144.
- [3] S. Ye, J. Feng, P. Wu, *ACS Appl. Mater. Interfaces* 5 (2013) 7122.

Acknowledgements

This work was supported by the Danish Research for Technology and Product Science (Project No. 12-127447). R.S.D. acknowledges a Hans C. Ørsted Postdoc Fellowship honored by Technical University of Denmark.